

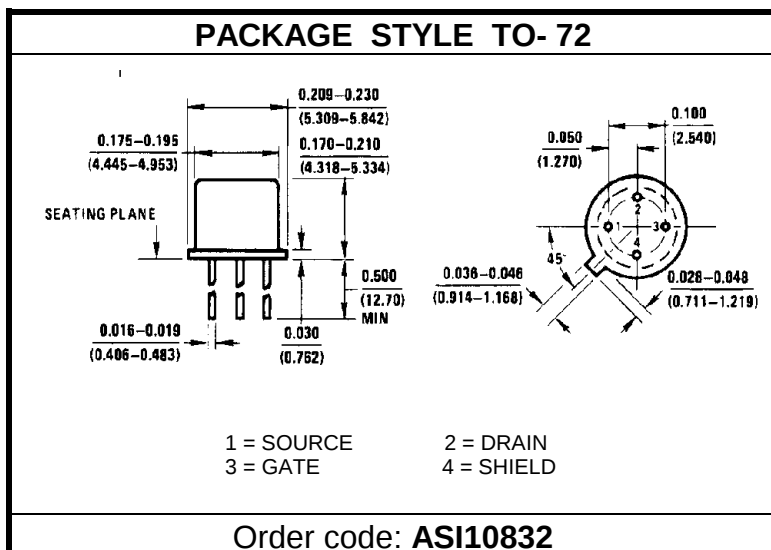
N-CHANNEL SILICON FET DEPLETION MODE

DESCRIPTION:

The **ASI BFW13** is Designed for Low Noise Video Amplifier Applications.

MAXIMUM RATINGS

I_D	10 mA
I_G	5.0 mA
V_{DS}	30 V
V_{DG}	30 V
V_{GS}	30 V
P_{tot}	150 mW @ $T_A = 110^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JA}	590 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{GS}	$V_{GS} = 10\text{ V}$ $T_C = 150^\circ\text{C}$			100 100	pA nA
I_{DSS}	$V_{DS} = 15\text{ V}$ $V_{GS} = 0\text{ V}$	0.2		1.5	mA
V_{GS}	$V_{DS} = 15\text{ V}$ $I_D = 50\text{ }\mu\text{A}$	0.1		1.0	V
$V_{(P)GS}$	$V_{DS} = 15\text{ V}$ $I_D = 500\text{ pA}$			1.2	V
$ y_{fs} $ $ y_{os} $	$V_{DS} = 15\text{ V}$ $V_{GS} = 0\text{ V}$	1500		10	μS
$ y_{fs} $ $ y_{os} $	$V_{DS} = 15\text{ V}$ $I_D = 200\text{ }\mu\text{A}$ $f = 1.0\text{ MHz}$	500		5.0	μS
C_{iss} C_{rs}	$V_{DS} = 15\text{ V}$ $f = 1.0\text{ MHz}$			5.0 0.8	pF
V_n	$V_{DS} = 15\text{ V}$ $I_D = 200\text{ }\mu\text{A}$ $BW = 0.6\text{ to }100\text{ Hz}$			500	nV